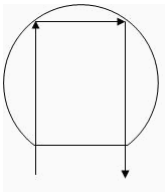
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	Customer supplied
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Customer supplied
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Customer supplied
	4.0	Secondary Flat Orientation	none / semi std	Customer supplied
	5.0	Overall Thickness	410.00 +/- 21.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	FZ	Customer supplied
	12.0	Handle Orientation	{100} +/- 1.0 degree	Customer supplied
	13.0	Handle Thickness	400.00 +/- 20.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Customer supplied
	15.0	Handle Dopant	Phosphorous	Customer supplied
	16.0	Handle Resistivity	50 ~ 60 Ohmcm	Customer supplied
	17.0	Backside Finish	Polished with oxide and lasermark	
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	35,000.00 +/- 3,500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and/or device wafer	
DeviceSilicon	21.0	Device Growth Method	FZ	Customer supplied
	22.0	Device Orientation	{100} +/- 1.0 degree	Customer supplied
	23.0	Nominal Thickness	6.50 +/- 1.00 µm	Filmetrics 9 point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	25.0	Device Doping Type	N	Customer supplied
	26.0	Device Dopant	Phosphorous	Customer supplied
	27.0	Device Resistivity	50 ~ 60 Ohmcm	Customer supplied
	28.0	Voids	0	Bright Light, 100% (note 2)
	29.0	Scratches	0	Bright Light, 100% (note 2)
	30.0	Haze	none	Bright Light, 100% (note 2)

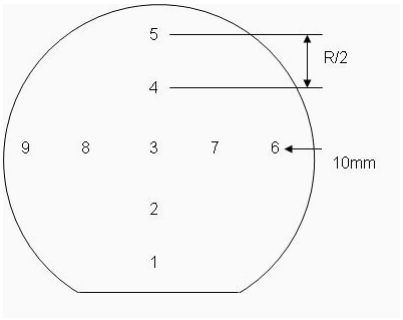
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information